

DEPOSITION OXIDE WITH IMPROVED OXYGEN BONDING

ABSTRACT OF THE INVENTION

5 A deposition oxide interface with improved oxygen bonding and a method for bonding oxygen in an oxide layer are provided. The method includes depositing an M oxide layer where M is a first element selected from a group including elements chemically defined as a solid and having an oxidation state in a range of +2 to +5, plasma oxidizing the M oxide layer at a temperature of less than 400° C using a high density plasma source, and in response to plasma oxidizing the M oxide layer, improving M-oxygen bonding in the M oxide layer. The plasma oxidation process diffuses excited oxygen radicals into the oxide layer. The plasma oxidation is performed at specified parameters including temperature, 10 power density, pressure, process gas composition, and process gas flow. In some aspects of the method, M is silicon, and the oxide interface is 15 incorporated into a thin film transistor.